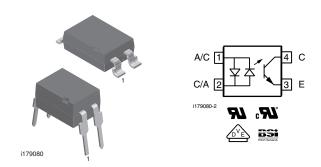


Vishay Semiconductors

# Optocoupler, Phototransistor Output, AC Input



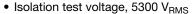
#### **DESCRIPTION**

The SFH620A (DIP) and SFH6206 (SMD) feature a high current transfer ratio, low coupling capacitance and high isolation voltage. These couplers have a GaAs infrared diode emitter, which is optically coupled to a silicon planar phototransistor detector, and is incorporated in a plastic DIP-4 or SMD package.

The coupling devices are designed for signal transmission between two electrically separated circuits. The couplers are end-stackable with 2.54 mm lead spacing. Creepage and clearance distances of > 8 mm are achieved with option 6. This version complies with IEC 60950 (DIN VDE 0805) for reinforced insulation to an operation voltage of 400  $V_{RMS}$  or DC.

### **FEATURES**

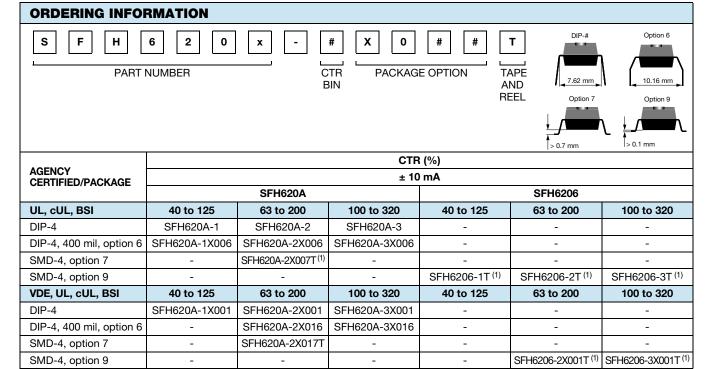
 Good CTR linearity depending on forward current



- High collector emitter voltage, V<sub>CEO</sub> = 70 V
- Low saturation voltage
- Fast switching times
- Low CTR degradation
- Temperature stable
- Low coupling capacitance
- End-stackable, 0.100" (2.54 mm) spacing
- High common-mode interference immunity
- Compliant to RoHS Directive to 2002/95/EC and in accordance WEEE 2002/96/EC

### **AGENCY APPROVALS**

- UL1577, file no. E52744 system code H, double protection
- CSA 93751
- BSI IEC 60950; IEC 60065
- DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-5-5 (pending), avialable with option 1



#### Note

- Additional options may be possible, please contact sales office.
- (1) Also available in tubes; do not add T to end.





# SFH620A, SFH6206

# Vishay Semiconductors Optocoupler, Phototransistor Output, AC Input



<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
INPUT						
DC forward current		I <sub>F</sub>	± 60	mA		
Surge forward current	t <sub>p</sub> ≤ 10 μs	I <sub>FSM</sub>	± 2.5	Α		
Power dissipation		P <sub>diss</sub>	100	mW		
OUTPUT						
Collector emitter voltage		V <sub>CE</sub>	70	V		
Emitter collector voltage		V <sub>EC</sub>	7	V		
Collector current		I <sub>C</sub>	50	mA		
Collector current	t <sub>p</sub> ≤ 1 μs	I <sub>C</sub>	100	mA		
Power dissipation		P <sub>diss</sub>	150	mW		
COUPLER						
Isolation test voltage between emitter and detector	t = 1 s	V <sub>ISO</sub>	5300	$V_{RMS}$		
Isolation voltage		$V_{IORM}$	890	$V_P$		
Total power dissipation		P <sub>tot</sub>	250	mW		
Creepage distance			≥ 7	mm		
Clearance distance			≥ 7	mm		
Insulation thickness between emitter and detector			≥ 4	mm		
Comparative tracking index per DIN IEC112/ VDE 0303, part 1		СТІ	175			
Indiation undistance	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 25 °C	R <sub>IO</sub>	≥ 10 <sup>12</sup>	Ω		
Isolation resistance	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 100 °C	R <sub>IO</sub>	≥ 10 <sup>11</sup>	Ω		
Storage temperature range		T <sub>stg</sub>	- 55 to + 150	°C		
Ambient temperature range		T <sub>amb</sub>	- 55 to + 100	°C		
Junction temperature		Tj	100	°C		
Soldering temperature (1)	max. 10 s, dip soldering distance	T <sub>sld</sub>	260	°C		

#### **Notes**

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

(1) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
INPUT								
Forward voltage	$I_F = \pm 60 \text{ mA}$		$V_{F}$		1.25	1.65	V	
Capacitance	V <sub>R</sub> = 0 V, f = 1 MHz		Co		50		pF	
Thermal resistance			R <sub>thja</sub>		750		K/W	
OUTPUT								
Collector emitter capacitance	$V_{CE} = 5 \text{ V, f} = 1 \text{ MHz}$		C <sub>CE</sub>		6.8		pF	
Thermal resistance			R <sub>thja</sub>		500		°C/W	
COUPLER								
Collector emitter saturation voltage	$I_F = \pm 10 \text{ mA}, I_C = 2.5 \text{ mA}$		V <sub>CEsat</sub>		0.25	0.4	V	
Coupling capacitance			C <sub>C</sub>		0.2		pF	
		SFH620A-1	I <sub>CEO</sub>		2	50	nA	
		SFH6206-1	I <sub>CEO</sub>		2	50	nA	
Collector emitter leakage current	V - 10 V	SFH620A-2	I <sub>CEO</sub>		2	50	nA	
	V <sub>CE</sub> = 10 V	SFH6206-2	I <sub>CEO</sub>		2	50	nA	
		SFH620A-3	I <sub>CEO</sub>		5	100	nA	
		SFH6206-3	I <sub>CEO</sub>		5	100	nA	

### Note

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering
evaluation. Typical values are for information only and are not part of the testing requirements.
Still air, coupler soldered to PCB or base.



# Optocoupler, Phototransistor Output, Vishay Semiconductors AC Input

CURRENT TRANSFER RATIO (T <sub>amb</sub> = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
		SFH620A-1	CTR	40		125	%
		SFH6206-1	CTR	40		125	%
	V - 5 V I - + 10 mA	SFH620A-2	CTR	63		200 200 320	%
	$V_{CE} = 5 \text{ V}, I_{F} = \pm 10 \text{ mA}$	SFH6206-2	CTR	63		200	%
		SFH620A-3	CTR	100		320	%
		SFH6206-3	CTR	100		320	%
I <sub>C</sub> /I <sub>F</sub>		SFH620A-1	CTR	13	30		%
		SFH6206-1	CTR	13	30		%
$V_{CE} = 5 \text{ V}, I_{F} = \pm 1$	\/ - 5 \/   -   1 m \	SFH620A-2	CTR	22	45		%
	v <sub>CE</sub> = 5 v, I <sub>F</sub> = ± 1 mA	SFH6206-2	CTR	22	45		%
		SFH620A-3	CTR	34	70		%
		SFH6206-3	CTR	34	70		%

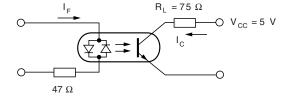


Fig. 1 - Switching Times Linear Operation (without Saturation)

<b>SWITCHING CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Turn-on time	$R_L = 75~\Omega,~I_F = \pm~10~mA,~V_{CC} = 5~V$	t <sub>on</sub>		3		μs	
Rise time	$R_L = 75 \Omega$ , $I_F = \pm 10$ mA, $V_{CC} = 5 V$	t <sub>r</sub>		2		μs	
Turn-off time	$R_L = 75 \Omega$ , $I_F = \pm 10$ mA, $V_{CC} = 5 V$	t <sub>off</sub>		2.3		μs	
Fall time	$R_L = 75~\Omega,~I_F = \pm~10~mA,~V_{CC} = 5~V$	t <sub>f</sub>		2		μs	
Cut-off frequency	$R_L = 75~\Omega, I_F = \pm~10~mA, V_{CC} = 5~V$	t <sub>ctr</sub>		250		kHz	

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Climatic classification (according to IEC 68 part 1)				55/100/21		
Comparative tracking index		CTI	175		399	
V <sub>IOTM</sub>			10 000			V
V <sub>IORM</sub>			890			V
P <sub>SO</sub>					400	mW
I <sub>SI</sub>					275	mA
T <sub>SI</sub>					175	°C
Creepage distance	Standard DIP-4		7			mm
Clearance distance	Standard DIP-4		7			mm
Creepage distance	400 mil DIP-4		8			mm
Clearance distance	400 mil DIP-4		8			mm
Insulation thickness, reinforced rated	per IEC 60950 2.10.5.1		0.4			mm

#### Note

As per IEC 60747-5-5, § 7.4.3.8.1, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with
the safety ratings shall be ensured by means of protective circuits.

# Vishay Semiconductors Optocoupler, Phototransistor Output, AC Input



## TYPICAL CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

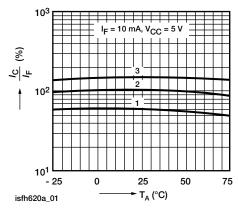


Fig. 2 - Current Transfer Ratio (CTR) vs. Temperature

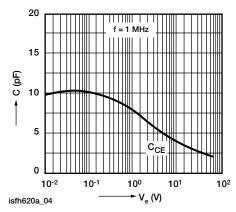


Fig. 5 - Transistor Capacitance (Typ.) vs. Collector Emitter Voltage

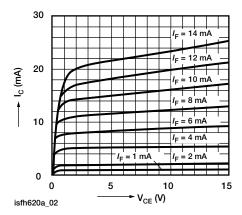


Fig. 3 - Output Characteristics (Typ.) Collector Current vs. Collector Emitter Voltage

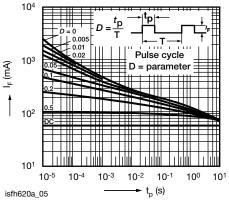


Fig. 6 - Permissible Pulse Handling Capability Forward Current vs. Pulse Width

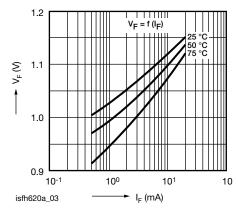


Fig. 4 - Diode Forward Voltage (Typ.) vs. Forward Current

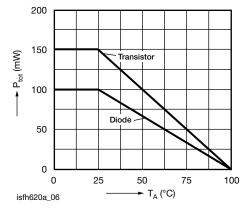


Fig. 7 - Permissible Power Dissipation vs. Ambient Temperature



# Optocoupler, Phototransistor Output, Vishay Semiconductors AC Input

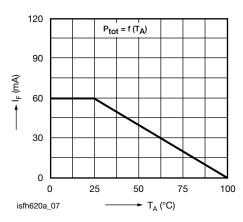
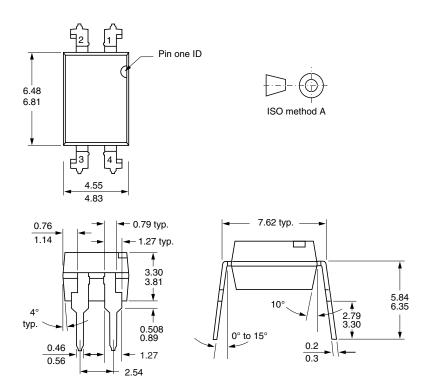


Fig. 8 - Permissible Diode Forward Current vs.
Ambient Temperature

### **PACKAGE DIMENSIONS** in millimeters

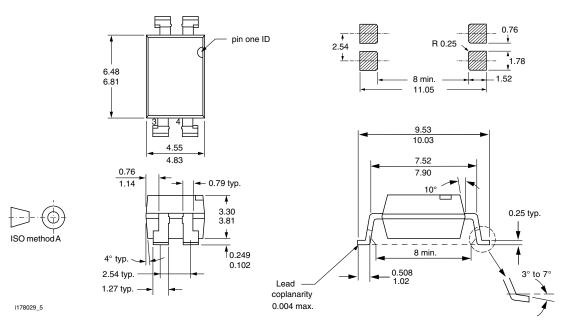


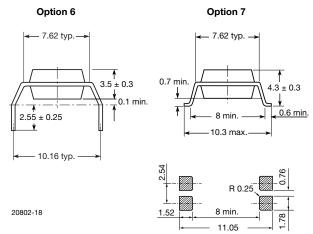
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# Vishay Semiconductors Optocoupler, Phototransistor Output, AC Input

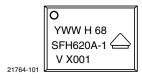


### **PACKAGE DIMENSIONS** in millimeters





### **PACKAGE MARKING** (example)



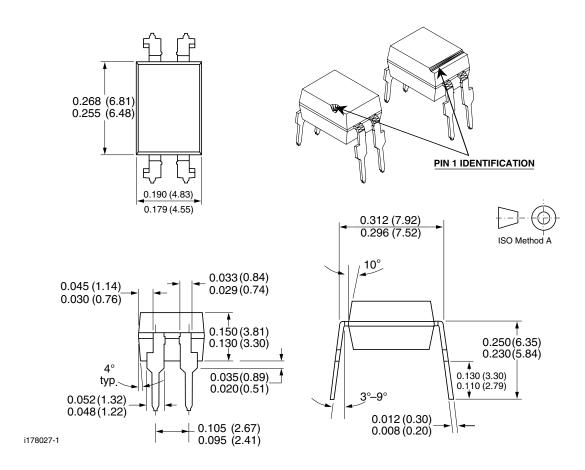
#### **Notes**

- Only options 1 and 7 are reflected in the package marking.
- The VDE Logo is only marked on option1 parts.
- Tape and reel suffix (T) is not part of the package marking.





# Package Dimensions in Inches (mm)



# TH-DIP-4

### **Vishay Semiconductors**



## Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

> We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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